CY54FCT373T, CY74FCT373T
8-BIT LATCHES
WITH 3-STATE OUTPUTS

- **Function and Pinout Compatible With FCT and F Logic**
- **Reduced V_{OH} (Typically = 3.3 V) Versions of Equivalent FCT Functions**
- **Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**
- **Matched Rise and Fall Times**
- **Fully Compatible With TTL Input and Output Logic Levels**
- **3-State Outputs**
- **CY54FCT373T**
  - **32-mA Output Sink Current**
  - **12-mA Output Source Current**
- **CY74FCT373T**
  - **64-mA Output Sink Current**
  - **32-mA Output Source Current**

CY54FCT373T . . . D PACKAGE
CY74FCT373T . . . Q OR SO PACKAGE
(TOP VIEW)

$\overline{OE}$	1		20	V_{CC}
O_0	2		19	O_7
D_0	3		18	D_7
D_1	4		17	D_6
O_1	5		16	O_6
O_2	6		15	O_5
D_2	7		14	D_5
D_3	8		13	D_4
O_3	9		12	O_4
GND	10		11	LE
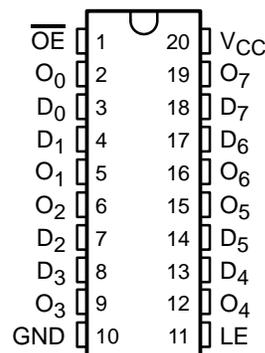
description

The 'FCT373T devices consist of eight latches with 3-state outputs for bus-organized applications. When the latch-enable (LE) input is high, the flip-flops appear transparent to the data. Data that meets the required setup times are latched when LE transitions from high to low. Data appears on the bus when the output-enable ($\overline{OE}$) input is low. When $\overline{OE}$ is high, the bus output is in the high-impedance state. In this mode, data can be entered into the latches.

These devices are fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TEXAS INSTRUMENTS

ORDERING INFORMATION

| T_A	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 85°C	QSOP – Q	Tape and reel	4.7	CY74FCT373CTQCT	FCT373C
	SOIC – SO	Tube	4.7	CY74FCT373CTSOC	FCT373C
		Tape and reel	4.7	CY74FCT373CTSOCT	
	QSOP – Q	Tape and reel	5.2	CY74FCT373ATQCT	FCT373A
	SOIC – SO	Tube	5.2	CY74FCT373ATSOC	FCT373
		Tape and reel	5.2	CY74FCT373ATSOCT	
	SOIC – SO	Tube	8	CY74FCT373TSOC	FCT373
		Tape and reel	8	CY74FCT373TSOCT	
−55°C to 125°C	CDIP – D	Tube	5.6	CY54FCT373ATDMB	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE}$	LE	D	O
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

H = High logic level, L = Low logic level,
X = Don't care, Z = High-impedance state,
Q_n = Previous state of flip flops (Q_{n-1})

logic diagram (positive logic)
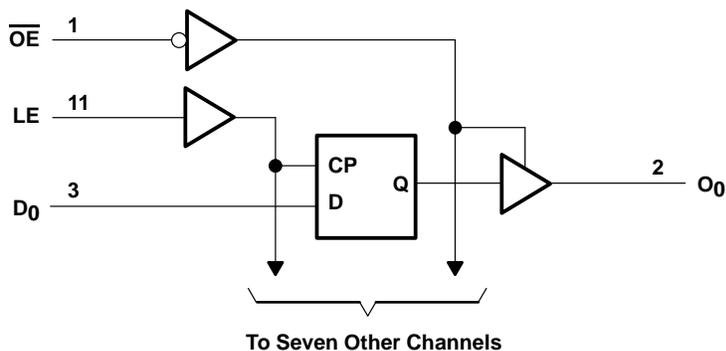
To Seven Other Channels

absolute maximum rating over operating free-air temperature range (unless otherwise noted)†

Supply voltage range to ground potential . . . . –0.5 V to 7 V
DC input voltage range . . . . –0.5 V to 7 V
DC output voltage range . . . . –0.5 V to 7 V
DC output current (maximum sink current/pin) . . . . 120 mA
Package thermal impedance, θ_{JA} (see Note 1): Q package . . . . 68°C/W
                                                                                  SO package . . . . 58°C/W
Ambient temperature range with power applied, T_A . . . . –65°C to 135°C
Storage temperature range, T_{stg} . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
NOTE 1: The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 2)

		CY54FCT373T			CY74FCT373T			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	4.5	5	5.5	4.75	5	5.25	V
V_{IH}	High-level input voltage	2			2			V
V_{IL}	Low-level input voltage			0.8			0.8	V
I_{OH}	High-level output current			–12			–32	mA
I_{OL}	Low-level output current			32			64	mA
T_A	Operating free-air temperature	–55		125	–40		85	°C

NOTE 2: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		CY54FCT373T			CY74FCT373T			UNIT
			MIN	TYP[†]	MAX	MIN	TYP[†]	MAX	
V_{IK}	$V_{CC} = 4.5$ V,	$I_{IN} = -18$ mA		−0.7	−1.2				V
	$V_{CC} = 4.75$ V,	$I_{IN} = -18$ mA					−0.7	−1.2	
V_{OH}	$V_{CC} = 4.5$ V,	$I_{OH} = -12$ mA	2.4	3.3					V
	$V_{CC} = 4.75$ V	$I_{OH} = -32$ mA				2			
		$I_{OH} = -15$ mA				2.4	3.3		
V_{OL}	$V_{CC} = 4.5$ V,	$I_{OL} = 32$ mA		0.3	0.55				V
	$V_{CC} = 4.75$ V,	$I_{OL} = 64$ mA					0.3	0.55	
V_{hys}	All inputs			0.2			0.2		V
I_I	$V_{CC} = 5.5$ V,	$V_{IN} = V_{CC}$			5				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = V_{CC}$						5	
I_{IH}	$V_{CC} = 5.5$ V,	$V_{IN} = 2.7$ V			±1				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = 2.7$ V						±1	
I_{IL}	$V_{CC} = 5.5$ V,	$V_{IN} = 0.5$ V			±1				µA
	$V_{CC} = 5.25$ V,	$V_{IN} = 0.5$ V						±1	
I_{OZH}	$V_{CC} = 5.5$ V,	$V_{OUT} = 2.7$ V			10				µA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 2.7$ V						10	
I_{OZL}	$V_{CC} = 5.5$ V,	$V_{OUT} = 0.5$ V			−10				µA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 0.5$ V						−10	
I_{OS}[‡]	$V_{CC} = 5.5$ V,	$V_{OUT} = 0$ V	−60	−120	−225				mA
	$V_{CC} = 5.25$ V,	$V_{OUT} = 0$ V				−60	−120	−225	
I_{off}	$V_{CC} = 0$ V,	$V_{OUT} = 4.5$ V			±1			±1	µA
I_{CC}	$V_{CC} = 5.5$ V,	$V_{IN} \leq 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V		0.1	0.2				mA
	$V_{CC} = 5.25$ V,	$V_{IN} \leq 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V					0.1	0.2	
ΔI_{CC}	$V_{CC} = 5.5$ V, $V_{IN} = 3.4$ V[§], $f_1 = 0$, Outputs open			0.5	2				mA
	$V_{CC} = 5.25$ V, $V_{IN} = 3.4$ V[§], $f_1 = 0$, Outputs open						0.5	2	

[†] Typical values are at $V_{CC} = 5$ V, $T_A = 25°$C.

[‡] Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

[§] Per TTL-driven input ($V_{IN} = 3.4$ V); all other inputs at V_{CC} or GND

TEXAS
INSTRUMENTS

POST OFFICE BOX 655303 ● DALLAS, TEXAS 75265

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS			CY54FCT373T			CY74FCT373T			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
I_{CCD}¶	V_{CC} = 5.5 V, Outputs open, One input switching at 50% duty cycle, $\overline{OE}$ = GND, $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V				0.06	0.12				mA/ MHz
	V_{CC} = 5.25 V, Outputs open, One input switching at 50% duty cycle, $\overline{OE}$ = GND, $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V							0.06	0.12	
I_C#	V_{CC} = 5.5 V, Outputs open, $\overline{OE}$ = GND, LE = V_{CC}	One bit switching at f_1 = 10 MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V		0.7	1.4				mA
			V_{IN} = 3.4 V or GND		1	2.4				
		Eight bits switching at f_1 = 2.5 MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V		1.3	2.6‖				
			V_{IN} = 3.4 V or GND		3.3	10.6‖				
	V_{CC} = 5.25 V, Outputs open, $\overline{OE}$ = GND, LE = V_{CC}	One bit switching at f_1 = 10 MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V					0.7	1.4	
			V_{IN} = 3.4 V or GND					1	2.4	
		Eight bits switching at f_1 = 2.5 MHz at 50% duty cycle	$V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{CC} - 0.2$ V					1.3	2.6‖	
			V_{IN} = 3.4 V or GND					3.3	10.6‖	
C_i					6	10		6	10	pF
C_o					8	12		8	12	pF

† Typical values are at V_{CC} = 5 V, T_A = 25°C.

¶ This parameter is derived for use in total power-supply calculations.

\# I_C = $I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD} (f_0/2 + f_1 \times N_1)$

Where:

I_C = Total supply current

I_{CC} = Power-supply current with CMOS input levels

ΔI_{CC} = Power-supply current for a TTL high input (V_{IN} = 3.4 V)

D_H = Duty cycle for TTL inputs high

N_T = Number of TTL inputs at D_H

I_{CCD} = Dynamic current caused by an input transition pair (HLH or LHL)

f_0 = Clock frequency for registered devices, otherwise zero

f_1 = Input signal frequency

N_1 = Number of inputs changing at f_1

All currents are in milliamperes and all frequencies are in megahertz.

‖ Values for these conditions are examples of the I_{CC} formula.

TEXAS INSTRUMENTS

POST OFFICE BOX 655303 ● DALLAS, TEXAS 75265

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		CY54FCT373T		CY54FCT373AT		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	6		6		ns
t_{su}	Setup time, data before LE↑	2		2		ns
t_h	Hold time, data after LE↑	1.5		1.5		ns

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		CY74FCT373T		CY74FCT373AT		CY74FCT373CT		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	6		5		5		ns
t_{su}	Setup time, data before LE↑	2		2		2		ns
t_h	Hold time, data after LE↑	1.5		1.5		1.5		ns

switching characteristics over operating free-air temperature range (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CY54FCT373AT		UNIT
			MIN	MAX	
t_{PLH}	D	O	1.5	5.6	ns
t_{PHL}	D	O	1.5	5.6	ns
t_{PLH}	LE	O	2	9.8	ns
t_{PHL}	LE	O	2	9.8	ns
t_{PZH}	$\overline{OE}$	O	1.5	7.5	ns
t_{PZL}	$\overline{OE}$	O	1.5	7.5	ns
t_{PHZ}	$\overline{OE}$	O	1.5	6.5	ns
t_{PLZ}	$\overline{OE}$	O	1.5	6.5	ns

switching characteristics over operating free-air temperature range (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CY74FCT373T		CY74FCT373AT		CY74FCT373CT		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	D	O	1.5	8	1.5	5.2	1.5	4.7	ns
t_{PHL}	D	O	1.5	8	1.5	5.2	1.5	4.7	ns
t_{PLH}	LE	O	2	13	2	8.5	2	5.5	ns
t_{PHL}	LE	O	2	13	2	8.5	2	5.5	ns
t_{PZH}	$\overline{OE}$	O	1.5	12	1.5	6.5	1.5	5.5	ns
t_{PZL}	$\overline{OE}$	O	1.5	12	1.5	6.5	1.5	5.5	ns
t_{PHZ}	$\overline{OE}$	O	1.5	7.5	1.5	5.5	1.5	5	ns
t_{PLZ}	$\overline{OE}$	O	1.5	7.5	1.5	5.5	1.5	5	ns

PARAMETER MEASUREMENT INFORMATION

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open
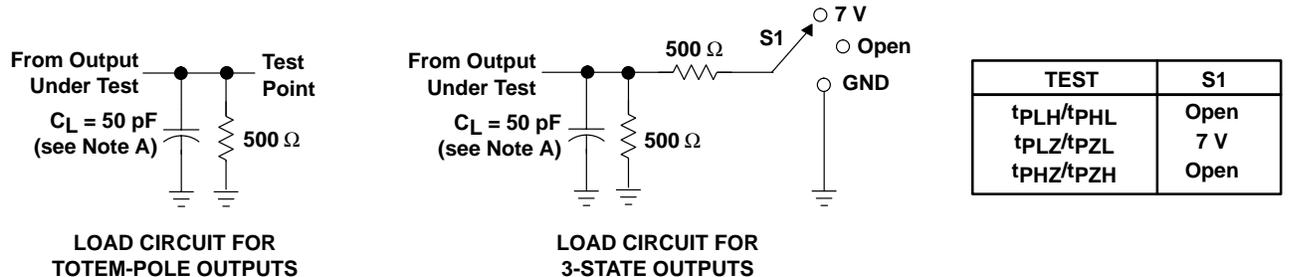
LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

LOAD CIRCUIT FOR
3-STATE OUTPUTS

VOLTAGE WAVEFORMS
PULSE DURATION

VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES

VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING
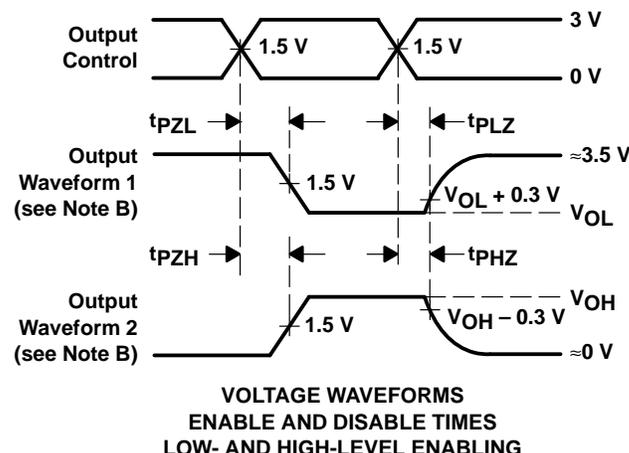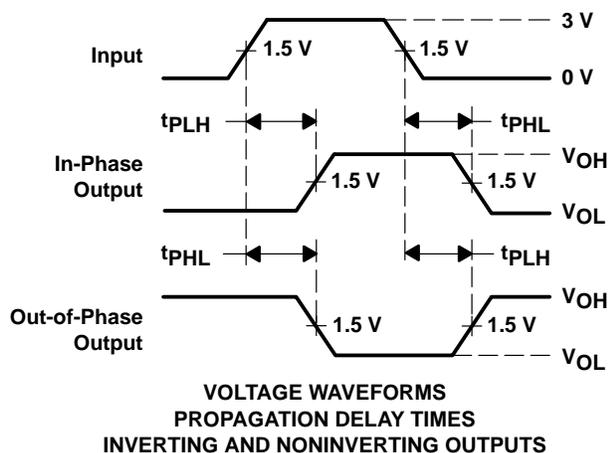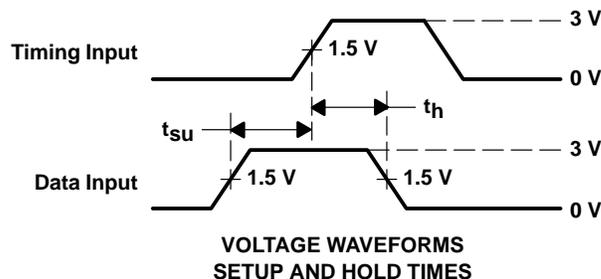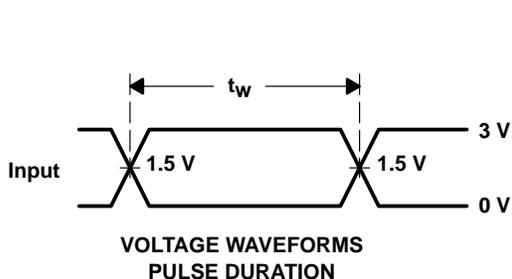
NOTES: A. C_L includes probe and jig capacitance.
        B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
            Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
        C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
5962-9221701MRA	ACTIVE	CDIP	J	20	1	TBD	A42 SNPB	N / A for Pkg Type
5962-9221702MRA	ACTIVE	CDIP	J	20	1	TBD	A42 SNPB	N / A for Pkg Type
5962-9221703M2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
CY54FCT373ATDMB	ACTIVE	CDIP	J	20	1	TBD	A42 SNPB	N / A for Pkg Type
CY74FCT373ATQCT	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373ATQCTE4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373ATQCTG4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373ATSOC	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373ATSOCE4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373ATSOCG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373ATSOCT	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373ATSOCTE4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373ATSOCTG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTQCT	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373CTQCTE4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373CTQCTG4	ACTIVE	SSOP/ QSOP	DBQ	20	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
CY74FCT373CTSOC	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTSOCE4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTSOCG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTSOCT	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTSOCTE4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373CTSOCTG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373TSOC	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373TSOCE4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373TSOCG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373TSOCT	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CY74FCT373TSOCTE4	ACTIVE	SOIC	DW	20	2000	Green (RoHS &	CU NIPDAU	Level-1-260C-UNLIM

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
						no Sb/Br)		
CY74FCT373TSOCTG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

[1] The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers
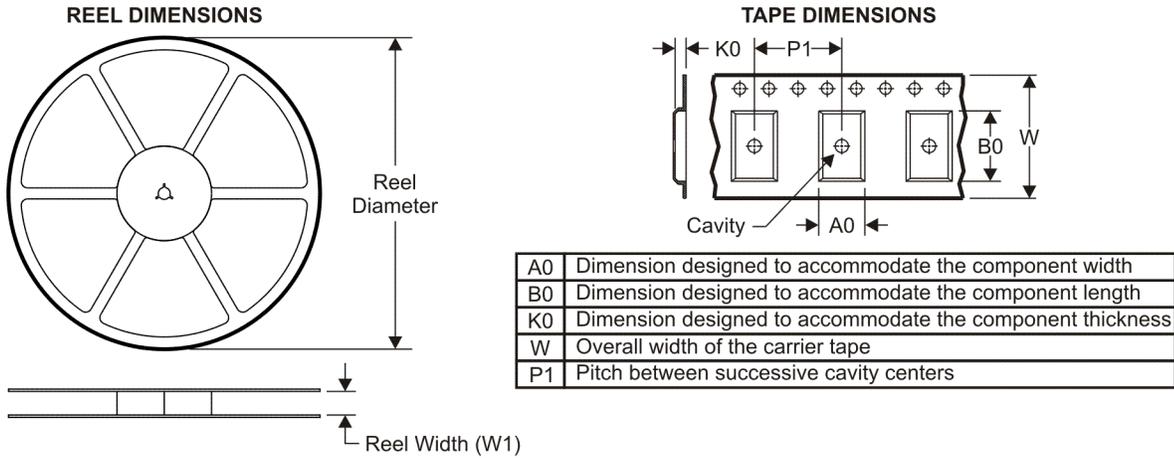
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE
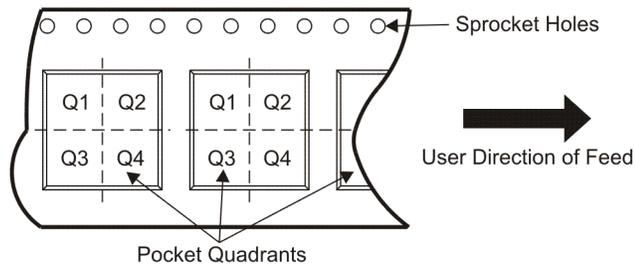
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT373ATQCT	SSOP/ QSOP	DBQ	20	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT373ATSOCT	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
CY74FCT373CTQCT	SSOP/ QSOP	DBQ	20	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT373CTSOCT	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
CY74FCT373TSOCT	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS
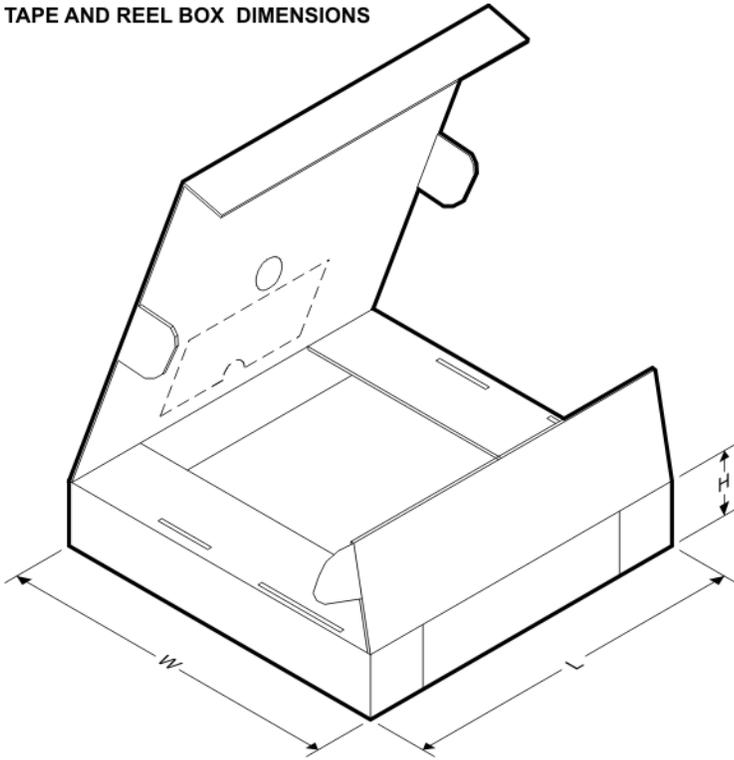
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT373ATQCT	SSOP/QSOP	DBQ	20	2500	346.0	346.0	33.0
CY74FCT373ATSOCT	SOIC	DW	20	2000	346.0	346.0	41.0
CY74FCT373CTQCT	SSOP/QSOP	DBQ	20	2500	346.0	346.0	33.0
CY74FCT373CTSOCT	SOIC	DW	20	2000	346.0	346.0	41.0
CY74FCT373TSOCT	SOIC	DW	20	2000	346.0	346.0	41.0

IMPORTANT NOTICE